IN THE CLAIMS:

The claims have not been amended, and are set forth here in full for the Examiner's convenience.

1. (Original) A stacked photovoltaic device comprising:

at least one pair of a first photovoltaic device and a second photovoltaic device stacked in order from a light incident side; and

a selective reflection layer formed between the at least one pair of the first photovoltaic device and the second photovoltaic device and adapted to electrically connect therebetween,

wherein the selective reflection layer has a sheet resistance of 100 kΩ/□ or more and 100 MΩ/□ or less.

2. (Original) The stacked photovoltaic device according to claim 1, wherein the selective reflection layer has a sheet resistance of 100 kΩ/□ or more and 50 MΩ/□ or less.

3. (Original) The stacked photovoltaic device according to claim 1, wherein the selective reflection layer has a sheet resistance of 5 MΩ/□ or more and 50 MΩ/□ or less.

4. (Original) The stacked photovoltaic device according to claim 1, wherein the selective reflection layer has a conductivity in a thickness direction of a film

which is larger than a conductivity in an in-plane direction of the film.

5. (Original) The stacked photovoltaic device according to claim 1, wherein the selective reflection layer comprises a deposited film formed of metal oxide.

6. (Original) The stacked photovoltaic device according to claim 1, wherein the first photovoltaic device has at least a pin-type junction and an i-type layer thereof comprises amorphous Si:H.

7. (Original) The stacked photovoltaic device according to claim 1, wherein the second photovoltaic device has at least a pin-type junction and an i-type layer thereof comprises Si having crystallinity.

8. (Original) The stacked photovoltaic device according to claim 1, wherein the second photovoltaic device has at least a pn-type junction and a p-type semiconductor and an n-type semiconductor comprise one of monocrystalline Si, polycrystalline Si, and Si having crystallinity.